TOSHIBA 1R5DL41

TOSHIBA HIGH EFFICIENCY RECTIFIER (HED) SILICON EPITAXIAL JUNCTION TYPE

R 5 D L 4 1

SWITCHING TYPE POWER SUPPLY APPLICATION

Repetitive Peak Reverse Voltage: V_{RRM} = 200 V

Average Forward Current $: I_{F(AV)} = 1.5 \text{ A (Ta} = 25^{\circ}\text{C)}$

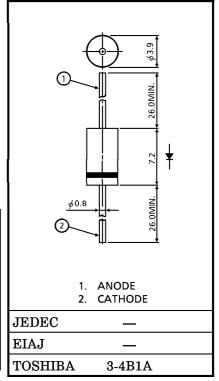
Very Fast Reverse-Recovery Time : $t_{rr} = 60 \text{ ns}$ (Max.)

Low Forward Voltage : $V_{FM} = 0.98 V \text{ (Max.)}$

Available to Reduce Switching Losses and Output Noise.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Reverse Voltage	V_{RRM}	200	V	
Average Forward Current (Ta = 25°C)	I _{F (AV)}	1.5	A	
Peak One Cycle Surge Forward Current (Non-Repetitive)	I_{FSM}	60 (50 Hz)	A	
Junction Temperature	$T_{ m j}$	-40~150	°C	
Storage Temperature	$\mathrm{T_{stg}}$	-40~150	°C	



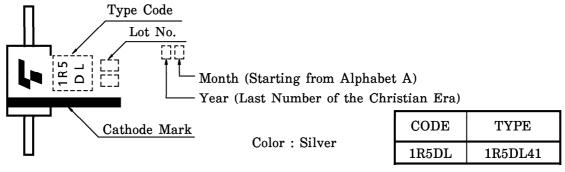
Unit in mm

Weight: 0.47 g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

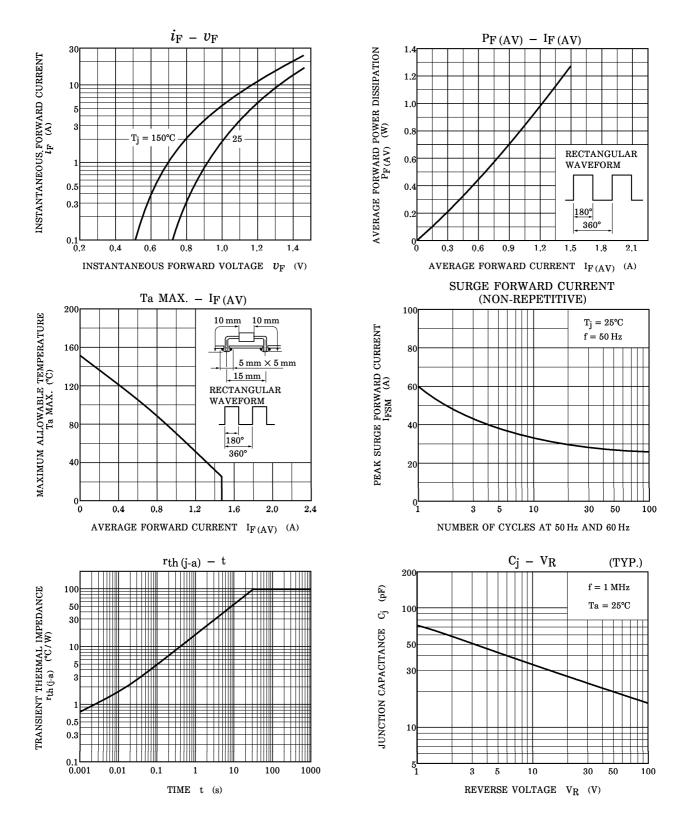
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	$V_{ extbf{FM}}$	$I_{\text{FM}} = 1.5 \text{ A}$	_	_	0.98	V
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM} = 200 V$	_	_	100	μ A
Reverse Recovery Time	t _{rr}	$I_{\rm F} = 2 {\rm A}, {\rm di} / {\rm dt} = -20 {\rm A} / \mu {\rm s}$	_	_	60	ns
Forward Recovery Time	t_{fr}	$I_{ m F}=1.0~{ m A}$	_	_	100	ns
Thermal Resistance	$R_{ ext{th }(j-a)}$	DC	_	_	100	°C/W
Thermal Resistance	$ m R_{th(j-\ell)}$	DC	_	_	30	°C/W

MARKING



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